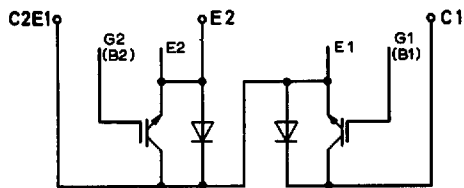
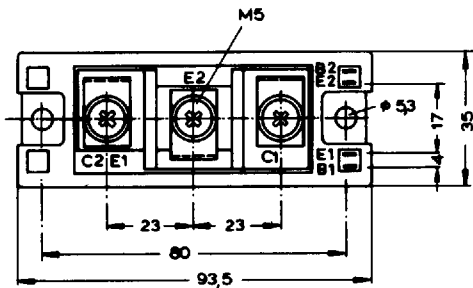
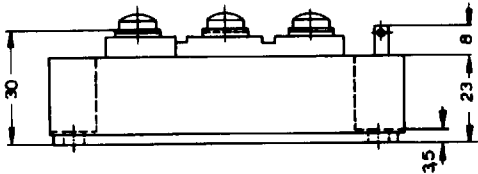


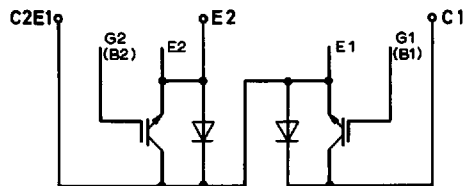
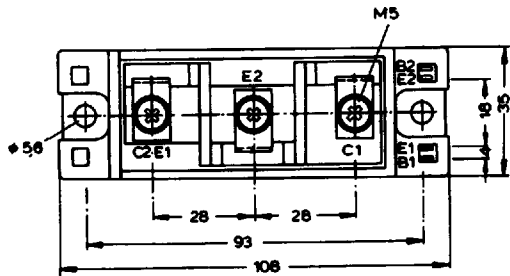
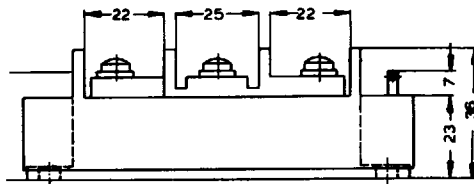
Transistor		Transistor		Thermische Eigenschaften		Thermal properties	
Elektrische Eigenschaften		Electrical properties		R _{thJC}	DC, pro Baustein / per module DC, pro Zweig / per arm	0,07 °C/W 0,417 °C/W	
Höchstzulässige Werte		Maximum rated values					
V _{CES}		600	V	t _{vjmax}		150	°C
I _C		100	A	t _{vjop}		-40 / +150	°C
I _{CRM}	t _p = 1 ms	200	A	t _{stg}		-40 / +125	°C
P _{tot}	t _C = 25°C	300	W	Inversdiode		Inverse diode	
V _{GE}		20	V	Elektrische Eigenschaften		Electrical properties	
V _{EG}		20	V	Höchstzulässige Werte		Maximum rated values	
Charakteristische Werte		Characteristic values		I _{F (max)}		100	A
V _{CE sat}	i _{CM} = 100 A, v _{GE} = 15 V, t _{vj} = 25°C	typ. 3	V	I _{FRM}	t _p = 1 ms	200	A
	i _{CM} = 100 A, v _{GE} = 15 V, t _{vj} = 25°C	max. 4	V	Charakteristische Werte		Characteristic values	
V _{GE (th)}	v _{CE} = 5 V, i _C = 100 mA, t _{vj} = 25°C	min. 3	V	v _F	i _F = 100 A, v _{GE} = 0 V, t _{vj} = 25°C	typ. 1,8	V
	v _{CE} = 5 V, i _C = 100 mA, t _{vj} = 25°C	max. 6	V		i _F = 100 A, v _{GE} = 0 V, t _{vj} = 25°C	max. 2,7	V
C _{GE}	v _{CE} = 10 V, v _{GE} = 0 V			I _{RM}	i _{FM} = 100 A, -di _F /dt = 100 A/μs		
	f _o = 1 MHz, t _{vj} = 25°C	typ. 7,4	nF		v _{EG} = 10 V, t _{vj} = 25°C	typ. 13	A
i _{CES}	v _{CE} = 600 V, v _{GE} = 0 V, t _{vj} = 25°C	typ. 0,5	mA		i _{FM} = 100 A, -di _F /dt = 100 A/μs		
	v _{CE} = 600 V, v _{GE} = 0 V, t _{vj} = 125°C	typ. 4	mA		v _{EG} = 10 V, t _{vj} = 125°C	typ. 22	A
i _{GES}	v _{GE} = 20 V, t _{vj} = 25°C	typ. 50	nA	Q _r	i _{FM} = 100 A, -di _F /dt = 100 A/μs		
	v _{GE} = 20 V, t _{vj} = 25°C	max. 500	nA		v _{EG} = 10 V, t _{vj} = 25°C	typ. 2	μAs
i _{EGS}	v _{EG} = 20 V, t _{vj} = 25°C	typ. 50	nA		i _{FM} = 100 A, -di _F /dt = 100 A/μs		
	v _{EG} = 20 V, t _{vj} = 25°C	max. 500	nA		v _{EG} = 10 V, t _{vj} = 125°C	typ. 6	μAs
t _{on}	i _{CM} = 100 A, v _{CE} = 300 V, v _{LF} = 15 V, R _G = 24 Ω, t _{vj} = 25°C	typ. 0,4	μs	Thermische Eigenschaften		Thermal properties	
	i _{CM} = 100 A, v _{CE} = 300 V, v _{LF} = 15 V, R _G = 24 Ω, t _{vj} = 125°C	typ. 0,5	μs	R _{thJC}	DC, pro Baustein / per module DC, pro Zweig / per arm	0,21 °C/W 1,25 °C/W	
t _s	i _{CM} = 100 A, v _{CE} = 300 V, v _{LF} = 15 V, v _{LR} = 15 V, R _G = 24 Ω, t _{vj} = 25°C	typ. 0,4	μs				
	i _{CM} = 100 A, v _{CE} = 300 V, v _{LF} = 15 V, v _{LR} = 15 V, R _G = 24 Ω, t _{vj} = 125°C	typ. 0,5	μs	t _{vjmax}		125	°C
t _f	i _{CM} = 100 A, v _{CE} = 300 V, v _{LF} = 15 V, v _{LR} = 15 V, R _G = 24 Ω, t _{vj} = 25°C	typ. 0,15	μs	t _{vjop}		-40 / +125	°C
	i _{CM} = 100 A, v _{CE} = 300 V, v _{LF} = 15 V, v _{LR} = 15 V, R _G = 24 Ω, t _{vj} = 125°C	typ. 0,25	μs	t _{stg}		-40 / +125	°C
Bedingungen für den Kurzschlußschutz		Conditions for protection against short circuits		Innere Isolation		Internal insulation	
t _{fg} = 10 μs, v _{LF} = v _{LR} = 15 V, R _G = 24 Ω, t _{vj} = 125°C,		V _{CC} = 350 V, V _{CEM} = 500 V, i _{CMK1} ≈ 500 A, i _{CMK2} ≈ 350 A		Isoliermaterial: AlN		Insulating material: AlN	
				V _{ISOL}	RMS	2,5	kV
				Mechanische Eigenschaften		Mechanical properties	
				G		500	g
				M1		3	Nm
				M2		3	Nm
				Maßbild		outline	
				Seite 124, Nr. 10		page 124, no. 10	

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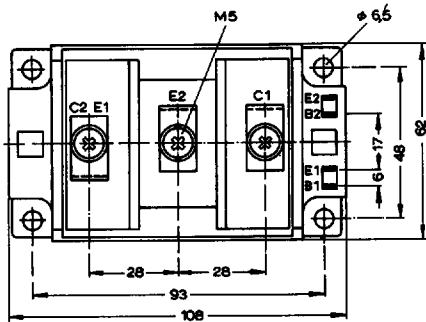
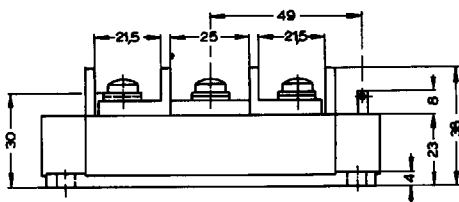
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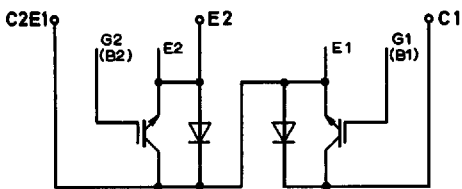
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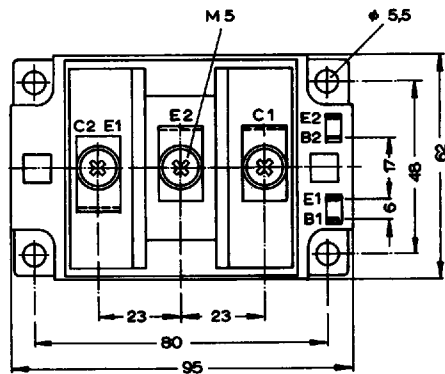
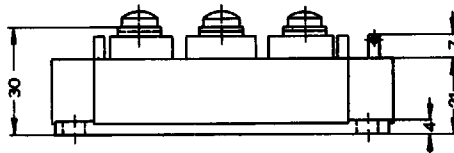


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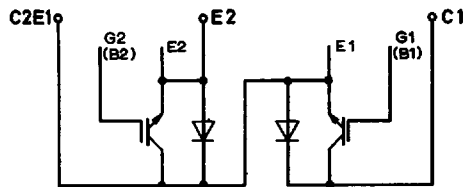


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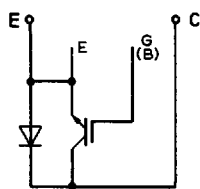
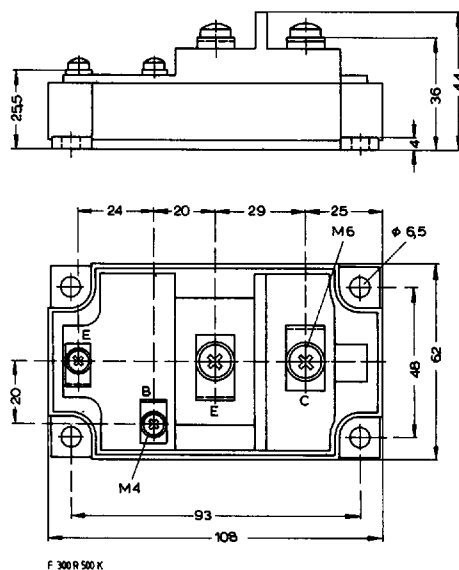
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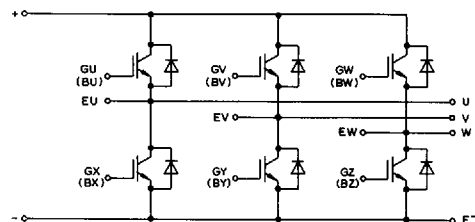
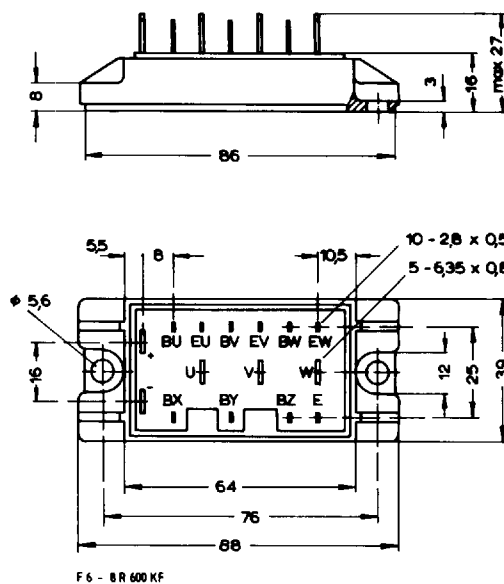
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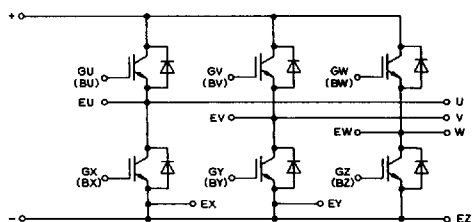
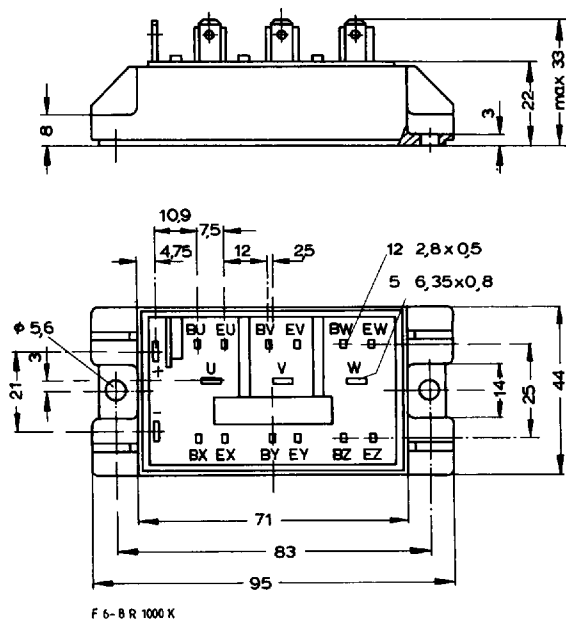
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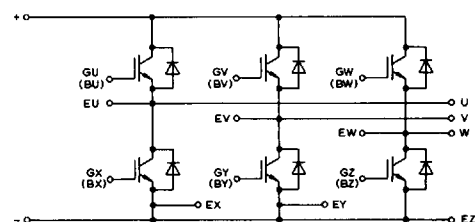
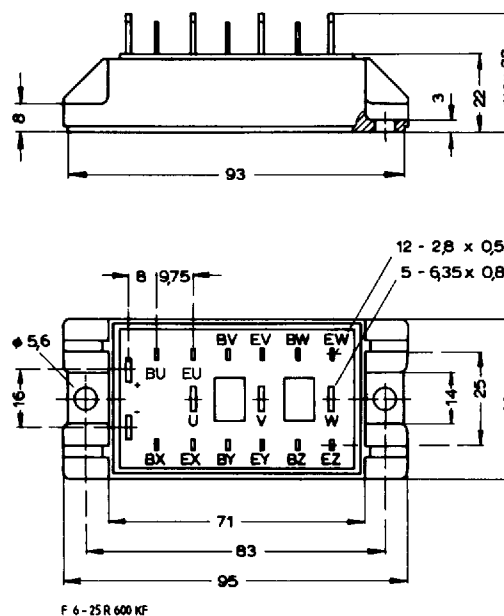
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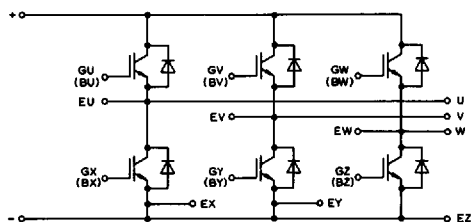
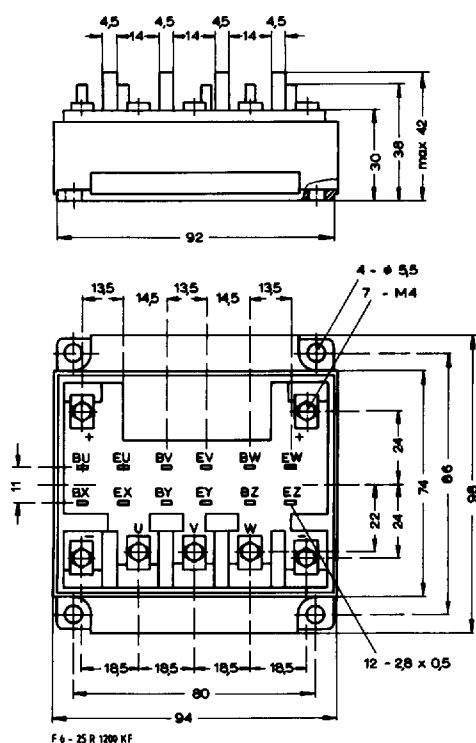
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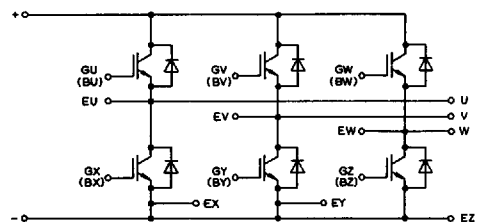
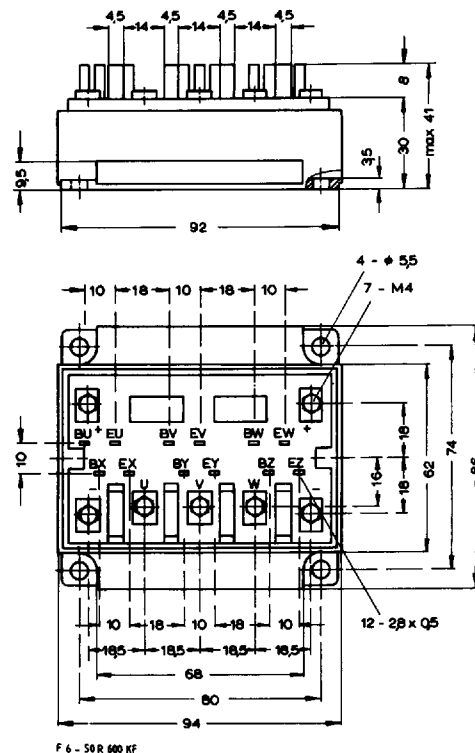
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